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ORNEY DOCKET NO.	ATT	FIRST NAMED INVENTOR	FILING DATE	APPLICATION NO.
EXAMINER		_		-
PAPER NUMBER	ART UNIT			
1				
DATE MAILED:				

Please find below and/or attached an Office communication concerning this application or proceeding.

**Commissioner of Patents and Trademarks** 

# Office Action Summary

Application No.

Applicant(s)

08/866,129

Uemura et al.

Examiner

Douglas Wille

Group Art Unit 2814



X Responsi	ive to communication(s) filed on <u>Sep 27, 199</u>	9	·
This action	ion is <b>FINAL</b> .		
	is application is in condition for allowance exc dance with the practice under <i>Ex parte Quayl</i> o		
is longer, fro	d statutory period for response to this action is om the mailing date of this communication. If to become abandoned. (35 U.S.C. § 133). E 36(a).	Failure to respond within the pe	riod for response will cause the
Disposition of	of Claims		
X Claim	n(s) 1, 2, 4-14, 20, and 21	is/a	re pending in the application.
Of the	e above, claim(s)	is/are	e withdrawn from consideration
	n(s)		
	n(s) 1, 2, 4-14, 20, and 21		
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	laims are subject to restriction or election requirement		
The di The pi The sp The o Priority unde Ackno All	he attached Notice of Draftsperson's Patent I I I I I I I I I I I I I I I I I I I	is approved iner.  priority under 35 U.S.C. § 119(appies of the priority documents in iner.)  priority under 35 U.S.C. § 129(appies of the priority documents in iner.)	a)-(d). have been  CT Rule 17.2(a)).
Inform Interv Notice	e of References Cited, PTO-892 mation Disclosure Statement(s), PTO-1449, P view Summary, PTO-413 e of Draftsperson's Patent Drawing Review, I e of Informal Patent Application, PTO-152		

--- SEE OFFICE ACTION ON THE FOLLOWING PAGES ---

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#### DETAILED ACTION

### Claim Rejections - 35 USC § 102

- 1. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
- 2. Claims 12 14 and 21 are rejected under 35 U.S.C. 102(e) as being anticipated by Nakamura et al.(\*422)
- 3. With respect to claims 12 14, Nakamura et al.(\*422) show a group III compound semiconductor device (see Figure 1) with a p-type upper layer 13 and an electrode consisting of a layer of Ni with a layer of Au on top (column 5, line 49). Figure 7 shows a modification of the Figure 1 device which has a contact layer 15 and a bonding pad 17 that covers part of layer 15 and has a protective film of silicon oxide (column 10, line 26). The other properties in claim 12 are inherent in the materials.
- 4. With respect to claim 21, Nakamura ('422) shows a structure with a AuNi layer covering part of a Ni and Au layer and will inherently have the same properties as claimed.

## Claim Rejections - 35 USC § 103

5. Claims 1, 2, 4 - 11, and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakamura et al.(\*422) in view of Manabe et al. and Nakamura et al.(\*350).

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- Nakamura et al. (\*422) show a group III compound semiconductor device (see Figure 1) 6. with a p-type upper layer 13 and an electrode consisting of a layer of Ni with a layer of Au on top (column 5, line 49). Figure 7 shows a modification of the Figure 1 device which has a contact layer 15 and a bonding pad 17 that covers part of layer 15 and has a protective film of silicon oxide (column 10, line 26). Nakamura et al. (422) show that the electrode layers are transparent (column 6, line 31). Nakamura et al. (422) also show that the bonding pad 17 is composed of Ni and Au but teach against the use of Al (in a two layer structure) since it can migrate to the electrode and can degrade it. Manabe et al. show the use of Al in a multilayer electrode stack (see Figure 6 and column 5, line 38) which has improved operating characteristics. It would have been obvious to modify the Nakamura et al.('422)device to include the Al layer as taught by Manabe et al. with the expectation that the two intervening layers will protect the electrode from deterioration. Nakamura et al. ('422) also teach annealing at 600 degrees (column 7, line 38) and teach the LED compound is In<sub>x</sub>Al<sub>x</sub>Ga<sub>1-x-x</sub>N. Nakamura et al. ('350) show that the silicon oxide protective layer is SiO<sub>2</sub> (column 34, line 66). The remainder of the claimed features are inherent in the choice of materials. Forming the layers in the sequence Ni-Au-Al follows the decreasing sequence of work functions and would also be obvious.
- 7. With respect to claim 20, Nakamura ('422) shows a structure with a AuNi layer covering part of a Ni and Au layer and will inherently have the same properties as claimed.

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#### **Conclusions**

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas A. Wille whose telephone number is (703) 308-4949.

9. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose number is (703) 308-0956.

Olik Chaudhuri Supervisory Patent Examiner Art Unit 2814

DAW & Sec

October 27, 1999